General Description

The WSF40P03 is the highest performance trench P-Ch MOSFET with extreme high cell density , which provide excellent RDSON and gate charge for most of the small power switching and load switch applications.

The WSF40P03 meet the RoHS and Green Product requirement with full function reliability approved.

Product Summery

BVDSS	RDSON	ID
-30V	15mΩ	-40A

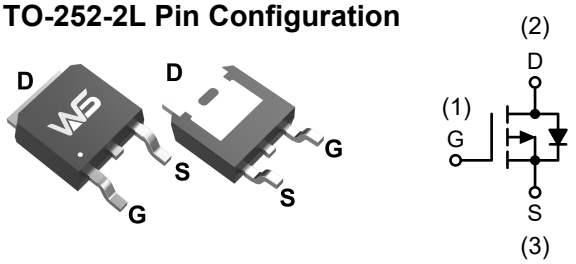
Applications

- Power Magagement in Desktop
- DC/DC Converters.
- Load Switch

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

TO-252-2L Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-30	V
V_{GS}	Gate-Source Voltage	±25	V
I_D@T_C=25℃	Continuous Drain Current, V_{GS} @ -10V	-40	A
I_D@T_C=100℃	Continuous Drain Current, V_{GS} @ -10V	-25	A
I_D@T_A=25℃	Continuous Drain Current, V_{GS} @ -10V	-9.6	A
I_D@T_A=70℃	Continuous Drain Current, V_{GS} @ -10V	-7.7	A
I_{DM} [a]	Pulsed Drain Current	-160	A
E_{AS} [b]	Single Pulse Avalanche Energy	28	mJ
I_{AS} [b]	Avalanche Current	-20	A
P_D@T_A=25℃	Total Power Dissipation	2.5	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$ [c]	Thermal Resistance Junction-Ambient	---	50	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-Case	---	2.9	℃/W

Note a：Pulse width limited by max. junction temperature.
Note b：UIS tested and pulse width limited by maximum junction temperature 150°C (initial temperature T_j=25°C).
Note c：Surface Mounted on 1in^2 pad area.

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=-250uA	-30	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BV_{DSS} Temperature Coefficient	Reference to 25℃ , I_D=-1mA	---	-0.022	---	V/℃
$R_{DS(ON)}$ [d]	Static Drain-Source On-Resistance[2]	V_{GS}=-10V , I_D=-20A	---	15	18	mΩ
		V_{GS}=-4.5V , I_D=-15A	---	20	26	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =-250uA	-1.2	-1.6	-2.5	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=-24V , V_{GS}=0V , T_J=25℃	---	---	-1	uA
		V_{DS}=-24V , V_{GS}=0V , T_J=55℃	---	---	-5	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	3.5	---	Ω
Q_g	Total Gate Charge	V_{DS}=-15V, V_{GS}=-4.5V, I_{DS}=-20A	---	11	---	nC
Q_{gs}	Gate-Source Charge		---	5	---	
Q_{gd}	Gate-Drain Charge		---	5	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=-15V, R_L=15Ω, I_{DS}=-1A, V_{GEN}=-10V, R_G=6Ω	---	10	20	ns
T_r	Rise Time		---	11	18	
$T_{d(off)}$	Turn-Off Delay Time		---	29	70	
T_f	Fall Time		---	39	53	
C_{iss} [e]	Input Capacitance	V_{GS}=0V, V_{DS}=-15V, Frequency=1.0MHz	---	1256	1633	pF
C_{oss} [e]	Output Capacitance		---	187	---	
C_{rss} [e]	Reverse Transfer Capacitance		---	115	---	

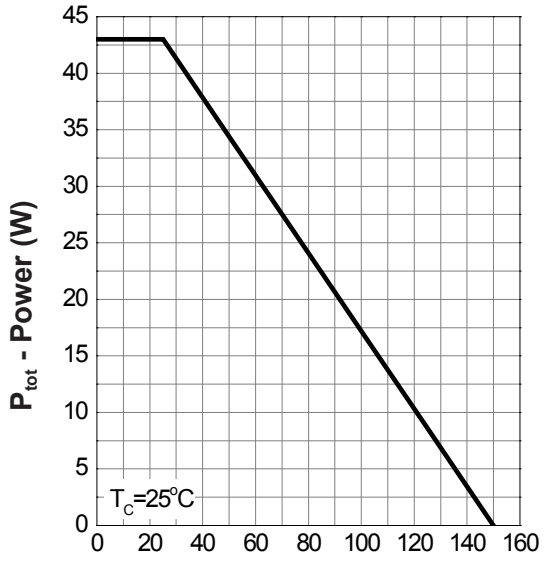
Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	V_G=V_D=0V , Force Current	---	---	-20	A
V_{SD} [d]	Diode Forward Voltage	V_{GS}=0V , I_S=-1A	---	---	-1.2	V
t_{rr}	Reverse Recovery Time	IF=-20A , dI/dt=100A/μs	---	12	---	nS
Q_{rr}	Reverse Recovery Charge		---	3.5	---	nC

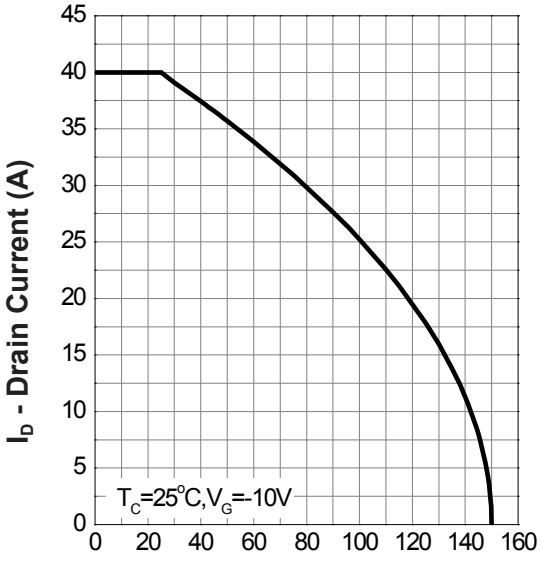
Note d：Pulse test ; pulse width≤300μs, duty cycle≤2%.
Note e：Guaranteed by design, not subject to production testing.

Typical Operating Characteristics

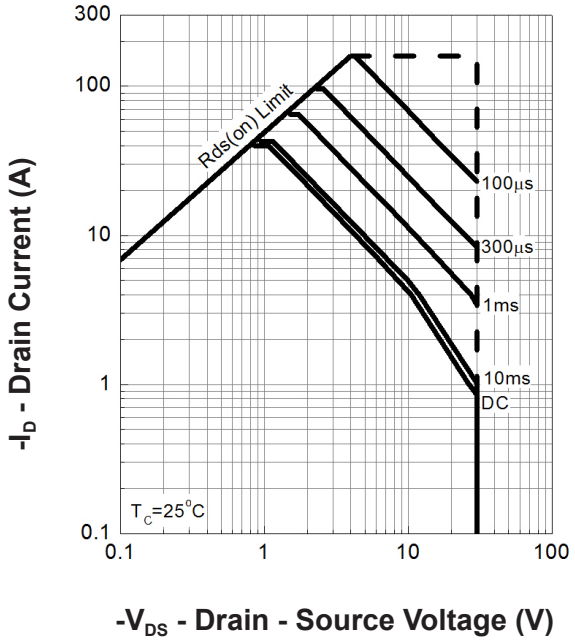
Power Dissipation



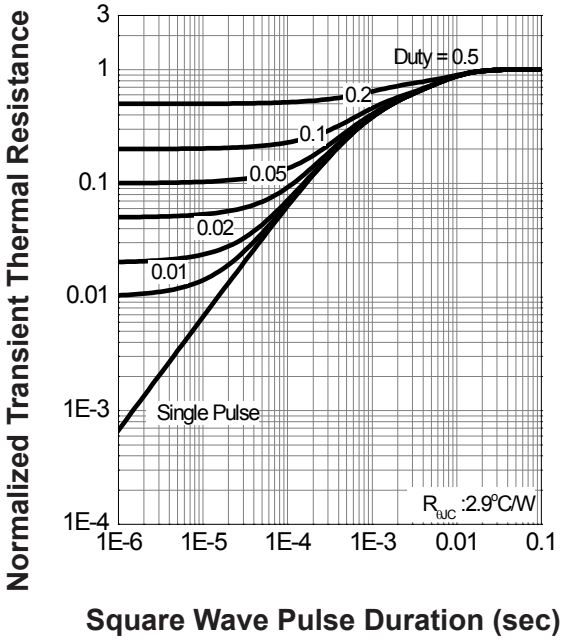
Drain Current



Safe Operation Area

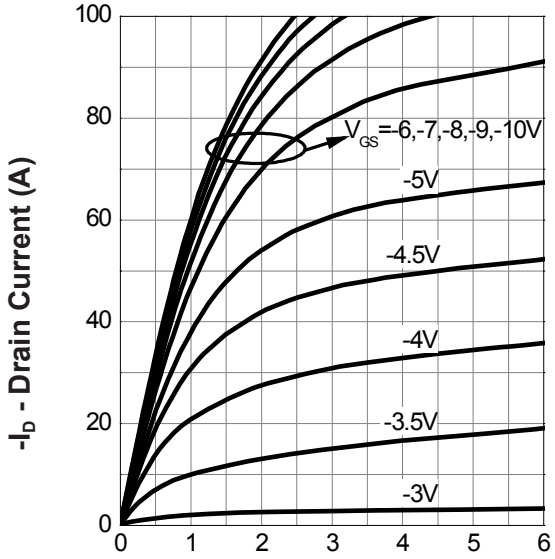


Thermal Transient Impedance

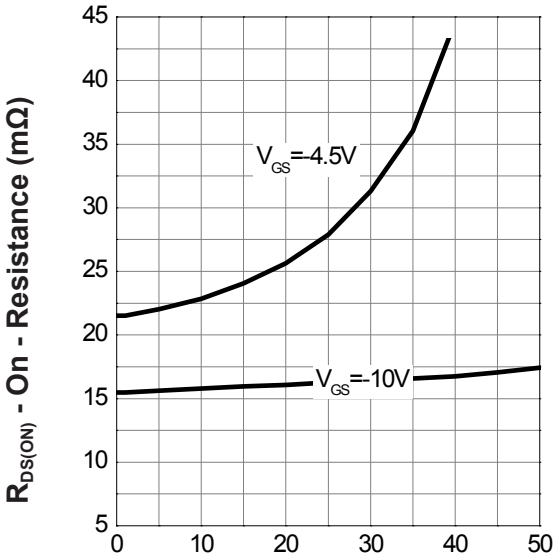


Typical Operating Characteristics(Cont.)

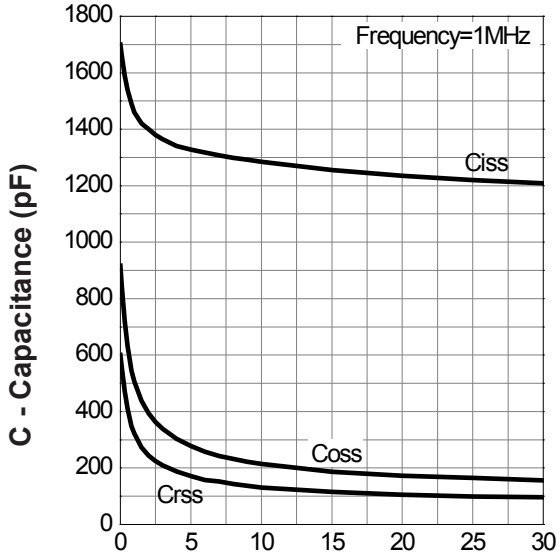
Output Characteristics



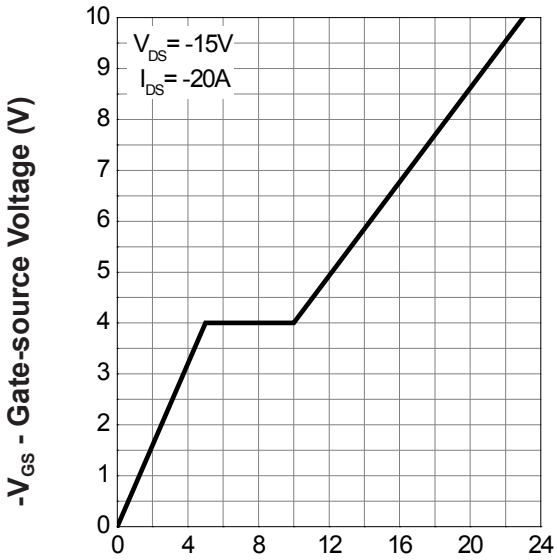
Drain-Source On Resistance



Capacitance

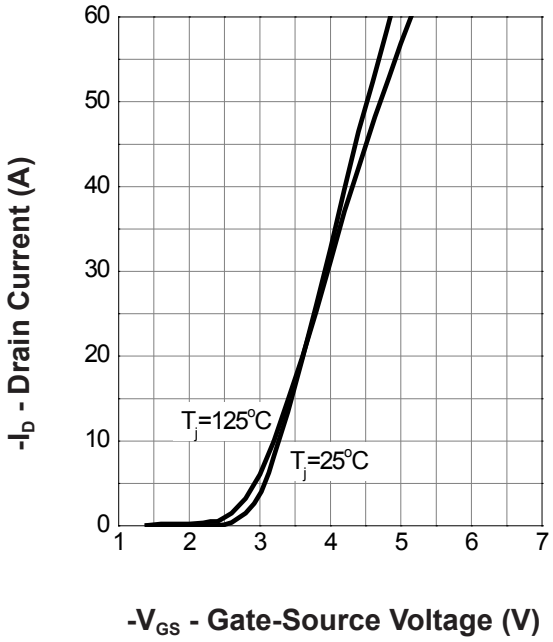


Gate Charge

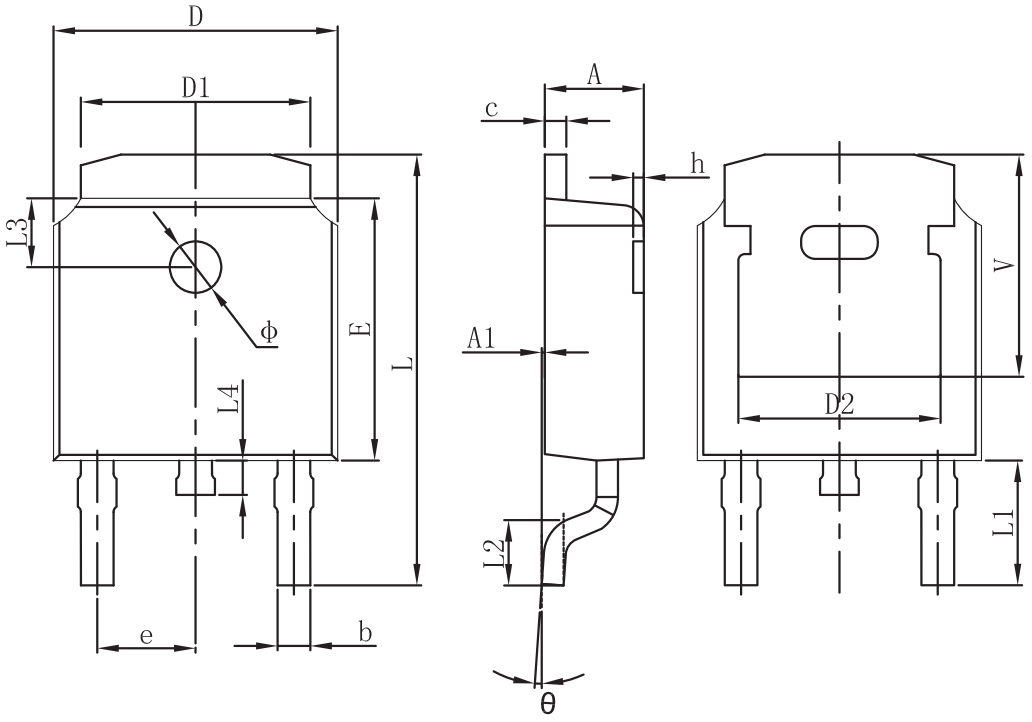


Typical Operating Characteristics(Cont.)

Transfer Characteristics



Packaging information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.635	0.770	0.025	0.030
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 REF.		0.190 REF.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.712	10.312	0.382	0.406
L1	2.900 REF.		0.114 REF.	
L2	1.400	1.700	0.055	0.067
L3	1.600 REF.		0.063 REF.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.250 REF.		0.207 REF.	

Attention

1, Any and all Winsok power products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your Winsok power representative nearest you before using any Winsok power products described or contained herein in such applications.

2,Winsok power assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all Winsok power products described or contained herein.

3, Specifications of any and all Winsok power products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.

4, Winsok power Semiconductor CO., LTD. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.

5,In the event that any or all Winsok power products(including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.

6, No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of Winsok power Semiconductor CO., LTD.

7, Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production. Winsok power believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.

8, Any and all information described or contained herein are subject to change without notice due to product/technology improvement,etc. When designing equipment, refer to the "Delivery Specification" for the Winsok power product that you Intend to use.

9, this catalog provides information as of Sep.2014. Specifications and information herein are subject to change without notice.